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Amendment to the Specification:

Please amend paragraph 14 to read as follows:

[0021] The gated charge-emission device 10 is, in general, a micro-fabricated device having an integrated gate (or gate electrode) 22 and an array 26 of emitters 30. "Integrated" means that the gate electrode 22 is part of the micro-fabricated structure that includes the emitters 30, and "micro-fabricated" means that the devices are made by techniques for fabricating structures with features that are microscopic. Examples of such techniques include, but are not limited to, semiconductor processing (e.g., for integrated circuits), chemical vapor deposition (e.g., for carbon nanotubes), and liquid chemistry (e.g., for nano-scale colloidal particles). Examples of charge-emission devices are described in United States Patent No. 3,789,471, issued to Spindt et al. on Feb. 5, 1974 and in United States Patent No. 6,362,574, issued to Agüero et al. on March 26, 2002, each of which patents ~~are~~ is incorporated by reference herein in their entirety.

Please amend paragraph 21 to read as follows:

[0021] In general, the protection circuitry 42 is any system, device or circuit that is capable of monitoring the emission current or other characteristics of the charge-emission device 10, of detecting an unwanted characteristic of the emission current, gate current, or other signal, and of responding to the detection of the unwanted characteristic by issuing a signal over signal path 70 that activates the current sink 38. Because the gate current is a general indicator of the charge-emission operation of the gated emitters 30, monitoring the gate current of the gated charge-emission device 10 can provide an early indicator of malfunction on the part of the emitters 30. The protection circuitry 42 and current sink 38 cooperate to provide a responsive mechanism for

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rapidly preventing any potentially damaging effect on the charge-emission device 10 by the unwanted emission characteristic.